Yuan Xie

List of Publications by Year
in descending order

16	718	858243 12	1051228 16
papers	citations	h-index	g-index

16	16	16	1347
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Modulation of MoTe₂/MoS₂ van der Waals heterojunctions for multifunctional devices using N₂O plasma with an opposite doping effect. Nanoscale, 2021, 13, 7851-7860.	2.8	5
2	Gate-tunable van der Waals heterostructure based on semimetallic WTe2 and semiconducting MoTe2. Applied Physics Letters, 2021, 118, .	1.5	10
3	Multi-level flash memory device based on stacked anisotropic ReS₂â€“boron nitrideâ€“graphene heterostructures. Nanoscale, 2020, 12, 18800-18806.	2.8	27
4	Non-volatile programmable homogeneous lateral MoTe2 junction for multi-bit flash memory and high-performance optoelectronics. Nano Research, 2020, 13, 3445-3451.	5.8	11
5	Multifunctional anti-ambipolar p-n junction based on MoTe2/MoS2 heterostructure. Applied Physics Letters, 2019, 115, .	1.5	35
6	Dynamically controllable polarity modulation of MoTe ₂ field-effect transistors through ultraviolet light and electrostatic activation. Science Advances, 2019, 5, eaav3430.	4.7	96
7	Gate-Tunable Photodetection/Voltaic Device Based on BP/MoTe₂ Heterostructure. ACS Applied Materials & Interfaces, 2019, 11, 14215-14221.	4.0	34
8	Photoinduced Doping To Enable Tunable and High-Performance Anti-Ambipolar MoTe₂/MoS₂ Heterotransistors. ACS Nano, 2019, 13, 5430-5438.	7.3	73
9	The effect of air stable n-doping through mild plasma on the mechanical property of WSe₂ layers. Nanotechnology, 2018, 29, 175703.	1.3	5
10	Specific and Highly Sensitive Detection of Ketone Compounds Based on p-Type MoTe₂ under Ultraviolet Illumination. ACS Applied Materials & Interfaces, 2018, 10, 35664-35669.	4.0	34
11	Acoustically enhanced photodetection by a black phosphorusâ€“MoS₂ van der Waals heterojunction pâ€“n diode. Nanoscale, 2018, 10, 10148-10153.	2.8	31
12	Ultrasensitive and Fully Reversible NO₂ Gas Sensing Based on p-Type MoTe₂ under Ultraviolet Illumination. ACS Sensors, 2018, 3, 1719-1726.	4.0	135
13	Enhancing electronic and optoelectronic performances of tungsten diselenide by plasma treatment. Nanoscale, 2018, 10, 12436-12444.	2.8	30
14	Highly sensitive MoTe ₂ chemical sensor with fast recovery rate through gate biasing. 2D Materials, 2017, 4, 025018.	2.0	125
15	Contact Engineering of Molybdenum Ditelluride Field Effect Transistors through Rapid Thermal Annealing. ACS Applied Materials & Interfaces, 2017, 9, 30107-30114.	4.0	37
16	Enhanced Sensitivity of MoTe2 Chemical Sensor through Light Illumination. Micromachines, 2017, 8, 155.	1.4	30